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(NE)  
Docket No. 740819-4087-24-01  
C. Wills

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of: )  
Hiroaki NAKAOKA et al. )  
Serial No. 09/640,519 )  
Filed: August 17, 2000 )  
For: METHOD OF FABRICATING )  
SEMICONDUCTOR DEVICE )

Examiner: D. Vu

Art Unit: 2818

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on July 16, 2001.

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated **January 19, 2001**, the period for response having been extended three (3) months to **July 19, 2001**, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 1, 2 and 8 as follows. Attached hereto is a marked-up copy of the amended claims.

1. (Amended) A method of fabricating a semiconductor device, the method comprising the steps of:

- (a) forming a silicon oxynitride film on a silicon substrate;
- (b) performing a heat treatment while keeping a surface of the silicon oxynitride film in contact with a gas containing nitrogen to introduce at least nitrogen into the silicon oxynitride film;
- (c) after step (b), forming a semiconductor film containing an impurity of first